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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/718,959	11/21/2003	Geun Su Lee	30205/39514	4436
4743 759	00 10/28/2005		EXAMINER	
MARSHALL, GERSTEIN & BORUN LLP			LEE, SIN J	
233 S. WACKER DRIVE, SUITE 6300 SEARS TOWER			ART UNIT	PAPER NUMBER
CHICAGO, IL 60606			1752	

DATE MAILED: 10/28/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
Office Action Summany	10/718,959	LEE, GEUN SU			
Office Action Summary	Examiner	Art Unit			
The MAILING DATE of this accommissation on	Sin J. Lee	1752			
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet with the	correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D.  - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATIO 136(a). In no event, however, may a reply be ti will apply and will expire SIX (6) MONTHS fron e, cause the application to become ABANDON	N. mely filed n the mailing date of this communication. ED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 08 A	August 2005.				
2a)☐ This action is <b>FINAL</b> . 2b)☑ Thi					
3) Since this application is in condition for allowa					
closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.			
Disposition of Claims					
4) ☐ Claim(s) 1-20 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) 4-7 is/are allowed. 6) ☐ Claim(s) 1-3,8 and 11-20 is/are rejected. 7) ☐ Claim(s) 9 and 10 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	own from consideration.				
Application Papers					
9)☐ The specification is objected to by the Examination  10)☒ The drawing(s) filed on 21 November 2003 is/s  Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct that the specific content is objected to by the Examination is objected to by the Examination is objected.	are: a)⊠ accepted or b)⊡ object drawing(s) be held in abeyance. Se ction is required if the drawing(s) is ob	ee 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119	•				
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureat* See the attached detailed Office action for a list	ts have been received. ts have been received in Applicat prity documents have been receiv tu (PCT Rule 17.2(a)).	tion No ed in this National Stage			
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal i 6) Other:				

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### **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

- 1. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 2. Claims 1, 3, 8, and 11-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Nishimura et al (EP 1 164 434 A2) (with Momota et al (US 2002/0172886 A1, which is being cited here to support the Examiner's position that the methylene group in the repeating unit (III-1) of Nishimura's Resin A-23 would not materially affect the basic and novel characteristic(s) of the present invention).

In Example 17 (see Table 1 of pg.54 and [0288]), Nishimura teaches a radiation sensitive resin composition containing 90 parts by weight of Resin A-23, 2.5 parts by weight of a photoacid generator, and 530 parts by weight of a solvent (propylene glycol monomethyl ether acetate). The Resin A-23 is described in [0277], and it has the following structure;

wherein the copolymerization molar ratio of the repeat unit (I-1) and (III-1) is 50:50. On pg.11, lines 30-53, Nishimura teaches the equivalence of the  $-CH_3$  in the  $\alpha$ -position of

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the repeat unit (III-1) and a hydrogen atom (see line 53 where it is stated that  $R^6$  represents a hydrogen atom or methyl group). Since there are only two choices for  $R^6$ , one of ordinary skill in the art would immediately envisage the repeat unit (III-1) shown above in which the –CH<sub>3</sub> group in the  $\alpha$ -position is replaced with a H atom, and the moiety of –C(CH<sub>3</sub>)(C(=O)-O-methyladamantyl)- in (III-1), in which –CH<sub>3</sub> group in the  $\alpha$ -position is replaced with a H atom, teaches present unit "b". Present unit "c" can be 0 mol%.

Although Nishimura's resin does contain –CH<sub>2</sub>- moiety, it is the Examiner's position that the prior art still teaches present photoresist polymer of claims 1 and 3 for the following reasons: Applicants use the transitional phrase "consisting essentially of" in present claim 1 (applicants are not using the transitional phrase "consisting of"). The phrase limits the scope of a claim to the specified materials "and those that do not materially affect the basic and novel characteristic(s)" of the claimed invention. See In re Herz, 537 F.2d 549, 551-52, 190 USPQ 461, 463 (CCPA 1976), as cited in MPEP 2111.03. The –CH<sub>2</sub>- moiety is generally known in the art as an inert group, for example, see Momota et al. [0049]. Therefore, it is the Examiner's position that the -CH<sub>2</sub>- moiety in Nishimura's resin would not materially affect the basic and novel characteristic(s) of the present invention. Besides, it was held in PPG Industries v. Guardian Industries, 156 F.3d 1351, 1355, 48 USPQ 2d 1351, 1355 that for the purposes of applying prior art under 35 USC 102 and 103, absent a clear indication in the specification or claims of what the basic and novel characteristics actually are, "consisting essentially of" will be construed as equivalent to "comprising.". Also, it was held in In re De Lajarte, 337 F.2d

870, 143 USPQ 256 (CCPA 1964) that if an applicant contends that additional materials in the prior art are excluded by the recitation of "consisting essentially of," *applicant* has the *burden* of showing that the introduction of additional components would materially change the characteristics of applicant's invention.

Therefore, for those reasons cited above, Nishimura teaches present inventions of claims 1, 3, 8, and 12.

With respect to present claim 11, since Nishimura uses 90 parts by weight of Resin A-23 and 2.5 parts by weight of a photoacid generator, this gives 2.8 wt.% of the photoacid generator based on the amount of the resin. Therefore, the prior art teaches present invention of claim 11.

With respect to present claim 13, since Nishimura uses 90 parts by weight of Resin A-23 and 530 parts by weight of the solvent, this gives 589 wt.% based on the amount of the resin. Therefore, the prior art teaches present invention of claim 13.

Nishimura teaches (see [0200]-[0204] and [0215]) that a resist pattern is formed from his radiation-sensitive resin composition by applying the composition solution to a substrate such as a silicon wafer to form a resist film, pre-baking the coated resist film, exposing it to radiation such as visible rays, UV rays, deep UV rays, X-rays, electron beams or the like (particularly preferable radiation being *ArF excimer laser* or *KrF excimer laser*), performing post-exposure bake at 90°C, and then developing the exposed resist film using an alkaline aqueous solution to form a predetermined resist pattern. Therefore, Nishimura teaches present inventions of claims 14-19 (since Nishimura teaches the same kinds of radiation source as the present invention, it is the

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Examiner's position that the prior art would inherently teach the present exposure energy range of claim 18).

With respect to present claim 20, Nishimura teaches ([0289]) that his radiation-sensitive resin composition is capable of producing semiconductors at a high yield without producing resolution defects during microfabrication. Therefore, the prior art teaches present invention of claim 20.

### Claim Rejections - 35 USC § 103

- 3. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
- 4. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nishimura et al (EP 1 164 434 A2).

In the Resin A-23 shown above, the repeat unit (III-1) has the 2-methyl-2-adamantyl group as the acid-labile group, and on pg.11, lines 30-50, lines 53-58, and [0066]-[0068], Nishimura teaches the equivalence of the 2-methyl-2-adamantyl group and t-butyl group (i.e., all R<sup>7</sup> groups of the formula (4) on pg.11 are methyl groups). Because the prior art teaches the equivalence of these two groups, it would have been obvious to one of ordinary skill in the art to replace the 2-methyl-2-adamantyl group in the repeat unit (III-1) of Resin A-23 with a t-butyl group (as an acid-labile group) with a reasonable expectation of obtaining a resin composition exhibiting high transmittance of radiation, high sensitivity, resolution, and pattern shape. Therefore, Nishimura's teaching would render obvious present invention of claim 2.

#### Allowable Subject Matter

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5. Claims 9 and 10 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Nishimura does not teach or suggest the use of present photoacid generator of claim 9 in combination with his inventive resin.

6. Claims 4-7 are allowed. Nishimura does not teach or suggest present method of forming the photoresist polymer of Formula 1.

#### Response to Arguments

7. Applicants argue that the photoresist polymer of amended claim 1 excludes a situation where one of the monomer moieties includes a methyl group off of the main chain as in Formula (III-1) of Nishimura and thus that the amended claim 1 is no longer anticipated by Nishimura. Applicants also argue that Nishimura's resin comprises repeat units of formulas I-1 (which comprises a polycyclic group) and III-1 which comprise a methacrylate group unit as the main chain and thus that Nishimura does not disclose a photoresist polymer that comprises a single carbon moiety having an ester group such as units b or c of amended claim 1.

However, as explained above, although Nishimura's resin does contain –CH<sub>2</sub>moiety, the prior art still teaches present photoresist polymer of amended claim 1
because it is the Examiner's position that the –CH<sub>2</sub>- moiety in Nishimura's resin would
not materially affect the basic and novel characteristic(s) of the present invention, in the
absence of applicant's showing that the introduction of –CH<sub>2</sub>- moiety would materially
change the characteristics of applicant's invention (applicants are not using the
transitional phrase "consisting of" which would exclude the presence of the –CH<sub>2</sub>-

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moiety in Nishimura's resin). Also, as explained above, Nishimura teaches the equivalence of the  $-CH_3$  in the  $\alpha$ -position of the repeat unit (III-1) and a hydrogen atom, and one of ordinary skill in the art would immediately envisage the repeat unit (III-1) shown above in which the  $-CH_3$  group in the  $\alpha$ -position is replaced with a H atom. The moiety of  $-C(CH_3)(C(=O)-O-methyladamantyl)-$  in (III-1), in which  $-CH_3$  group in the  $\alpha$ -position is replaced with a H atom, teaches present unit "b", and present unit "c" can be 0 mol%. Therefore, Nishimura does teach present photoresist polymer that comprises present unit b or c of amended claim 1.

For the reasons explained above, present rejections still stand.

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Sin J. Lee whose telephone number is 571-272-1333. The examiner can normally be reached on Monday-Friday from 9:00 am EST to 5:30 pm EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Cynthia Kelly, can be reached on 571-272-1526. The fax phone number for the organization where this application or proceeding is assigned is **571-273-8300**.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

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Business Center (EBC) at 866-217-9197 (toll-free).

S. Lee

October 25, 2005

SIN LEE PRIMARY EXAMINER

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